

said first interconnection includes a first interconnection extension portion extending beyond said outer peripheral trench to said potential fixing region,
 said second interconnection includes a second interconnection extension portion extending beyond said outer peripheral trench to said gate electrode,
 said first interconnection is electrically connected to said potential fixing region in said first interconnection extension portion, and
 said second interconnection is electrically connected to said gate electrode in said second interconnection extension portion.

5. The semiconductor device according to claim 1, wherein an angle formed between a sidewall surface of said trench and said one main surface is from 100° to 160°.

6. The semiconductor device according to claim 1, wherein said semiconductor substrate is composed of silicon carbide.

7. A method of manufacturing a semiconductor device, comprising the steps of:

preparing a semiconductor substrate including a drift layer having a first conductivity type and a body layer having a second conductivity type, which is formed on said drift layer to include one main surface;

forming a trench to open on a side of said one main surface and to penetrate said body layer and reach said drift layer;

forming a first insulating film to include a wall surface of said trench;

forming a gate electrode to be in contact with said first insulating film; and

forming a first interconnection on said one main surface, in said step of forming a trench, an outer peripheral trench arranged to surround an active region when viewed two-dimensionally being formed, and

in said step of forming a first interconnection, said first interconnection being formed to lie over said active region when viewed two-dimensionally and to electrically be connected to a potential fixing region which is said body layer exposed at said one main surface opposite to said active region when viewed from said outer peripheral trench.

8. The method of manufacturing a semiconductor device according to claim 7, wherein

in said step of forming a trench, said outer peripheral trench is formed simultaneously with said trench other than said outer peripheral trench.

9. The method of manufacturing a semiconductor device according to claim 7, further comprising the step of forming an electric field relaxing region having the second conductivity type, which extends to be in contact with said outer peripheral trench in said drift layer and to reach said potential fixing region, wherein

in said step of forming an electric field relaxing region, said electric field relaxing region is formed through ion implantation.

10. The method of manufacturing a semiconductor device according to claim 7, wherein

in said step of preparing a semiconductor substrate, a semiconductor substrate composed of silicon carbide is prepared.

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